

# RTE13LFM

Composite Transistor  
Zener Diode  
Silicon NPN Epitaxial Type

## DESCRIPTION

RTE13LFM is compound transistor built with 2SC3052 chip and 8.2V Zener diode in SC-88 package.

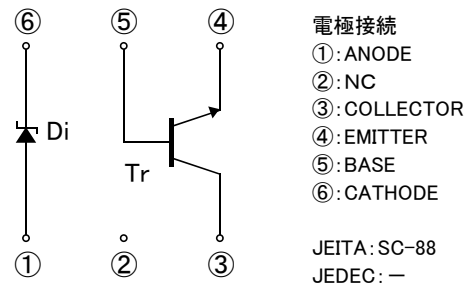
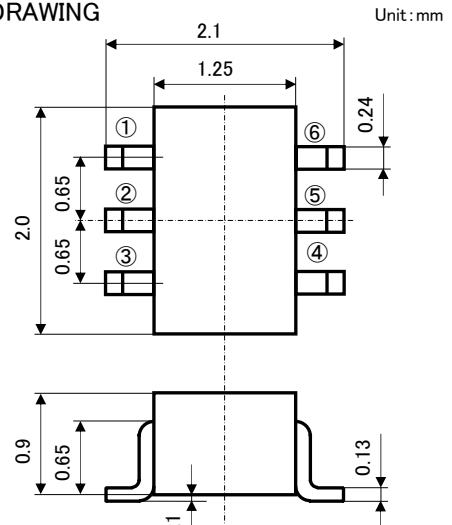
## FEATURE

- Silicon epitaxial type
- Each transistor elements are independent.
- Mini package for easy mounting

## APPLICATION

Power supply circuit, Driver circuit, etc

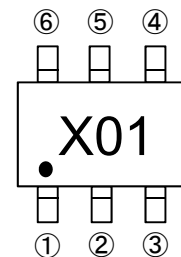
## OUTLINE DRAWING



## MAXIMUM RATING(Ta=25°C)

SYMBOL	PARAMETER		RATING	UNIT
V <sub>CB0</sub>	Collector to Base voltage	Tr	50	V
V <sub>CE0</sub>	Collector to Emitter voltage		50	V
V <sub>EB0</sub>	Emitter to Base voltage		6	V
I <sub>C</sub>	Collector current	Tr	200	mA
P <sub>T</sub>	Total power dissipation(Ta=25°C)		150	mW
T <sub>j</sub>	Junction temperature	Di	+150	°C
T <sub>stg</sub>	Storage temperature	Common	-55~+150	°C

## MARKING



## ELECTRICAL CHARACTERISTICS(Ta=25°C)

### 【 Tr 】

SYMBOL	PARAMETER	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
V <sub>(BR)CEO</sub>	Collector to Emitter break down voltage	I <sub>C</sub> =100μA, R <sub>BE</sub> =∞	50	-	-	V
I <sub>CB0</sub>	Collector cut off current	V <sub>CB</sub> =50V, I <sub>E</sub> =0A	-	-	0.1	μA
I <sub>EB0</sub>	Emitter cut off current	V <sub>EB</sub> =6V, I <sub>C</sub> =0A	-	-	0.1	μA
h <sub>FE</sub>	DC forward current gain	V <sub>CE</sub> =6V, I <sub>C</sub> =1mA	250	-	500	-
h <sub>FE</sub>	DC forward current gain	V <sub>CE</sub> =6V, I <sub>C</sub> =0.1mA	90	-	-	-
V <sub>CE(sat)</sub>	Collector to Emitter saturation voltage	I <sub>C</sub> =100mA, I <sub>B</sub> =10mA	-	-	0.3	V
f <sub>T</sub>	Gain band width product	V <sub>CE</sub> =6V, I <sub>E</sub> =-10mA	-	200	-	MHz
C <sub>ob</sub>	Collector output capacitance	V <sub>CB</sub> =6V, I <sub>E</sub> =0A, f=1MHz	-	2.5	-	pF

### 【 Di 】

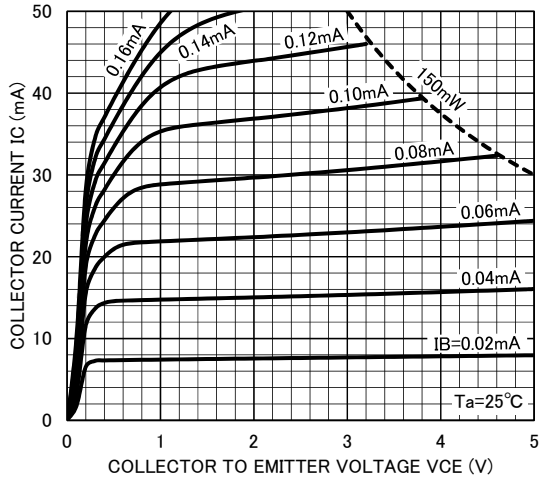
Zener voltage Vz(V)			Reverse current I <sub>R</sub> (μA)	
MIN	MAX	I <sub>Z</sub> (mA)	MAX	V <sub>R</sub> (V)
7.790	8.610	5	0.5	6.5

# RTE13LFM

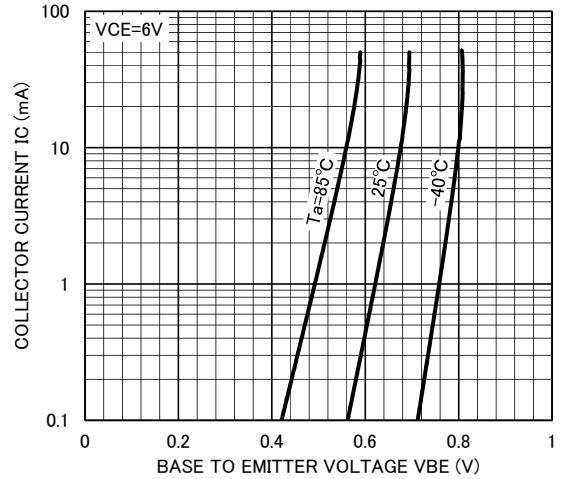
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## [Tr] TYPICAL CHARACTERISTICS

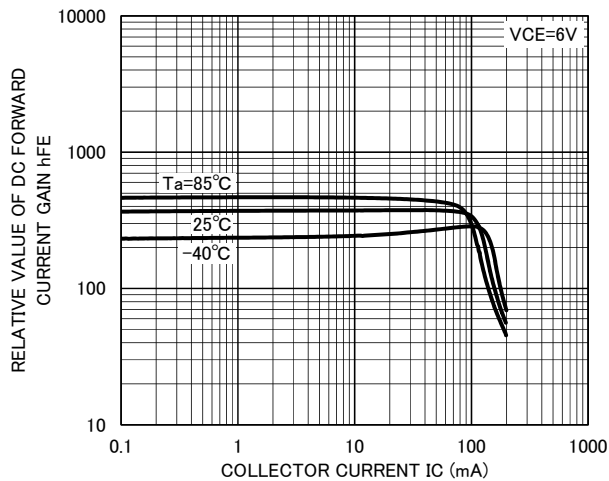
### COMMON EMITTER OUTPUT



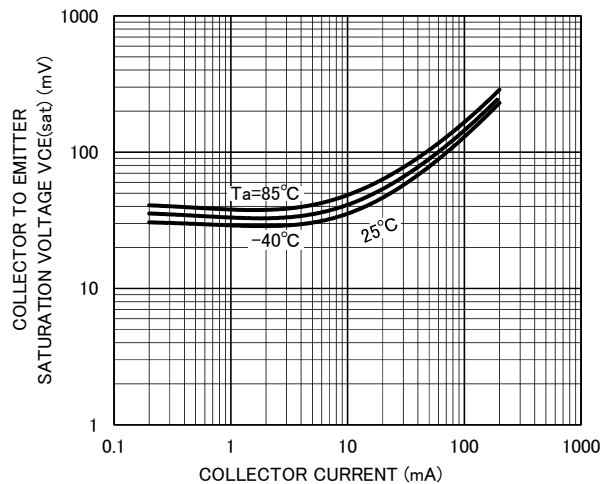
### COMMON EMITTER TRANSFER



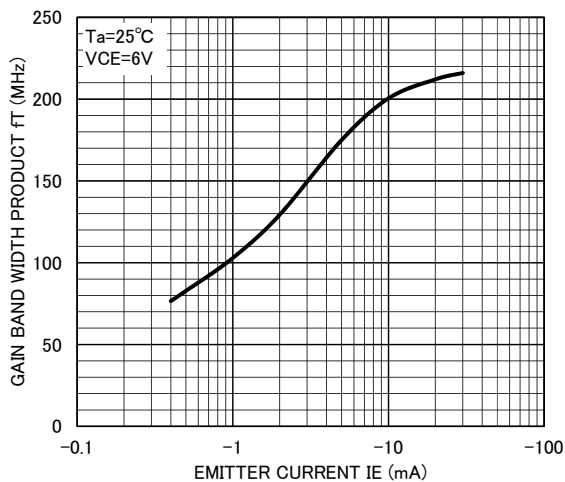
### hFE-IC



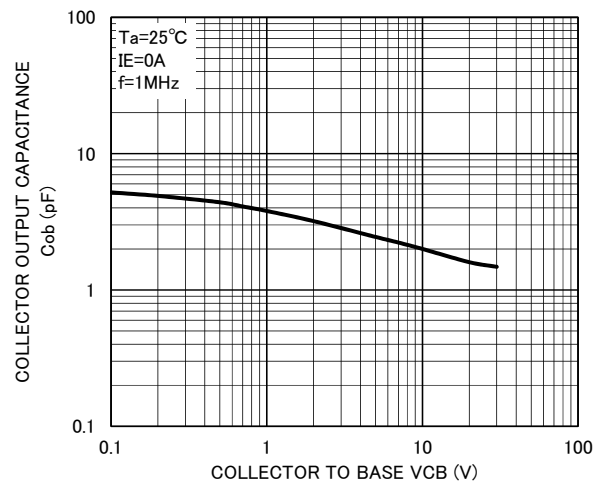
### VCE(sat)-IC



### fT-IE



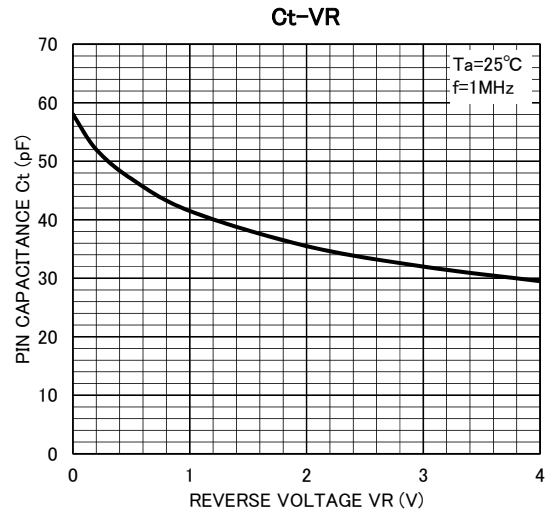
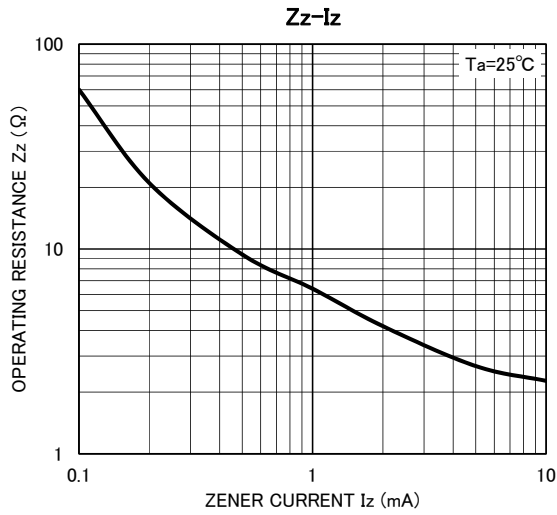
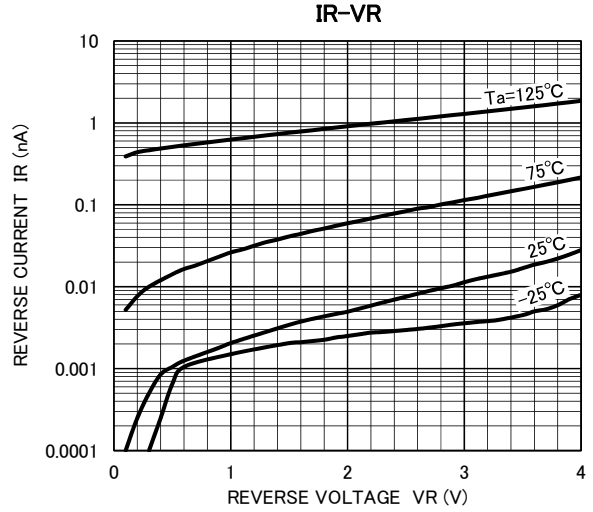
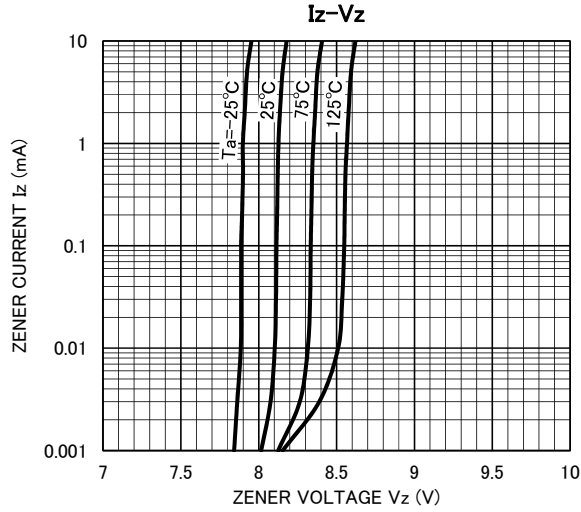
### Cob-VCB



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## 【Di】TYPICAL CHARACTERISTICS





6-41 Tsukuba, Isahaya, Nagasaki, 854-0065 Japan

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